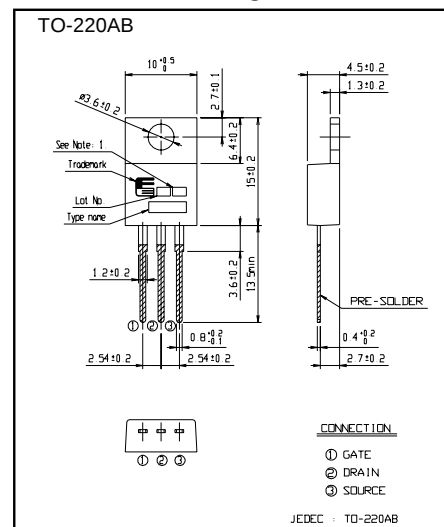


N-CHANNEL SILICON POWER MOSFET**FAP-III B SERIES****■ Features**

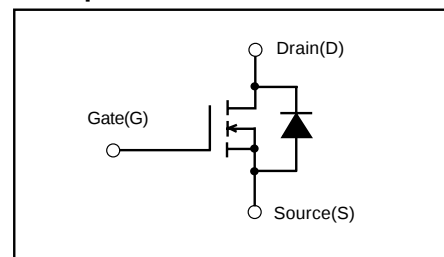
- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- High voltage
- Avalanche-proof

■ Applications

- Switching regulators
- DC-DC converters
- General purpose power amplifier

■ Outline Drawings**■ Maximum ratings and characteristics****● Absolute maximum ratings (Tc=25°C unless otherwise specified)**

Item	Symbol	Rating	Unit	Remarks
Drain-source voltage	V _{DS}	30	V	
Continuous drain current	I _D	±50	A	
Pulsed drain current	I _D [puls]	±200	A	
Gate-source peak voltage	V _{GS}	±16	V	
Maximum avalanche energy	E _{AV}	520	mJ	*1
Maximum power dissipation	P _D	60	W	
Operating and storage temperature range	T _{ch} T _{stg}	+150 -55 to +150	°C	

*1 L=0.277mH, V_{CC}=12V**■ Equivalent circuit schematic****● Electrical characteristics (T_c =25°C unless otherwise specified)**

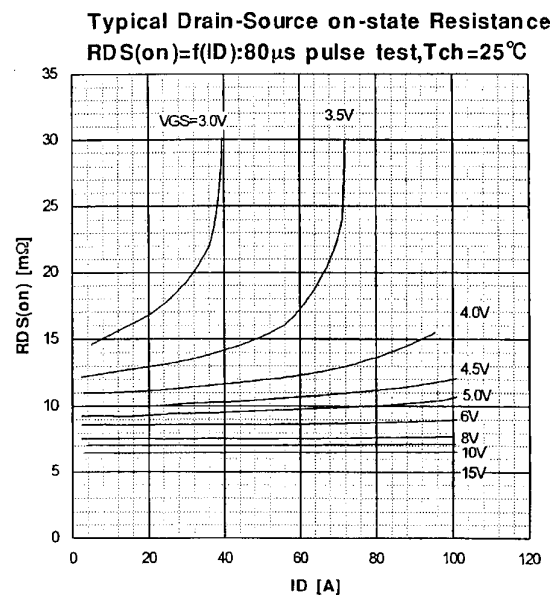
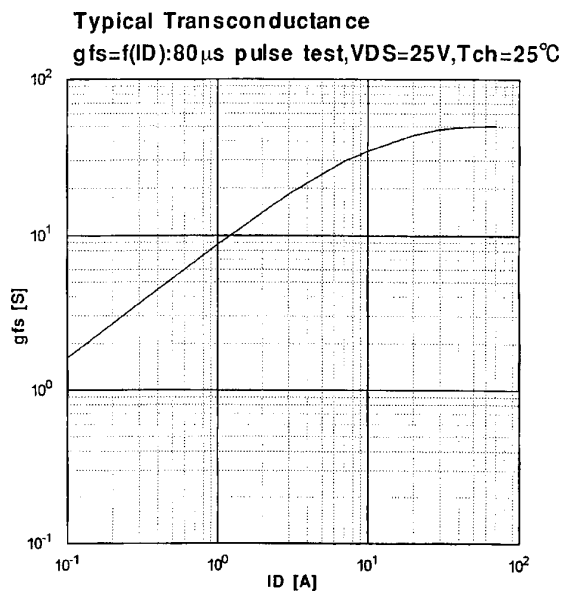
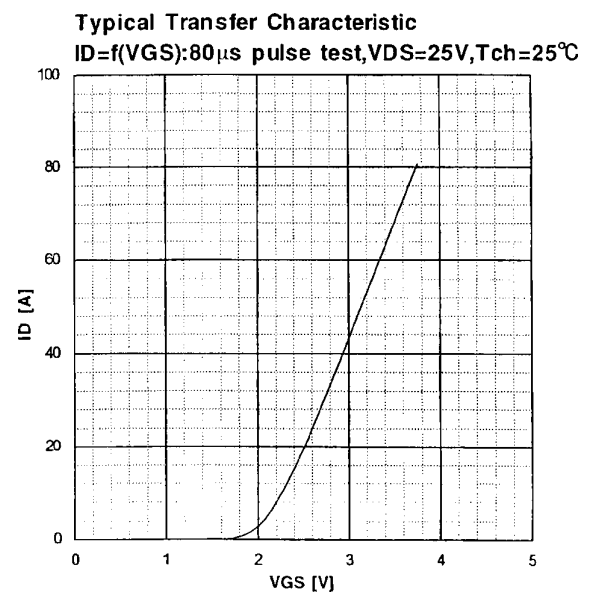
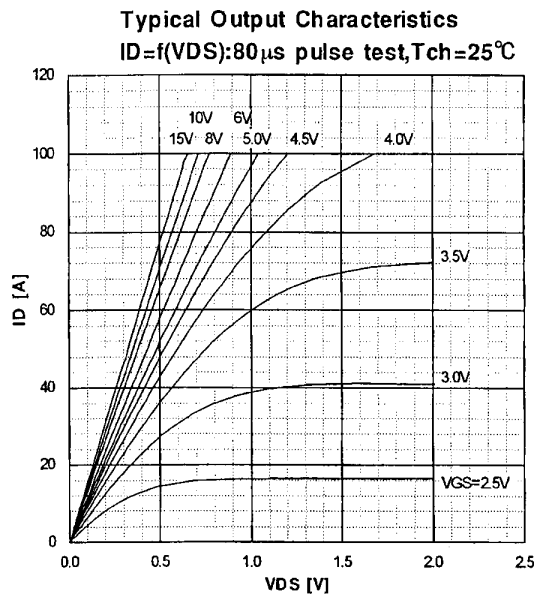
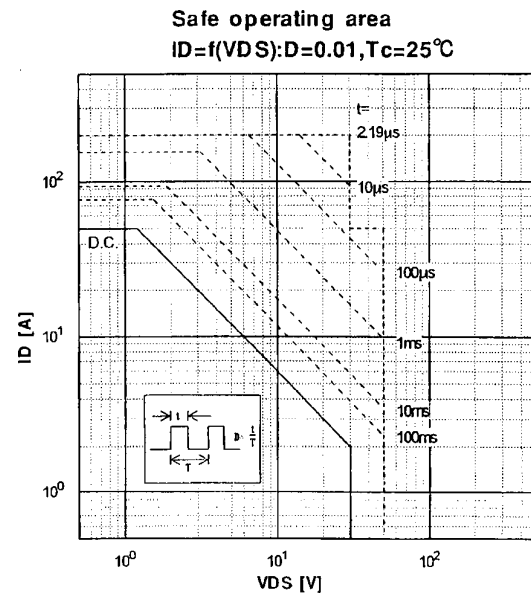
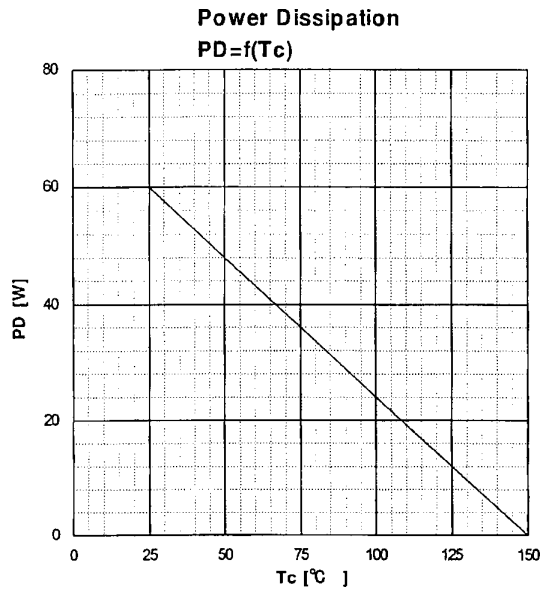
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =1mA V _{GS} =0V	30			V
Gate threshold voltage	V _{GS(th)}	I _D =1mA V _{DS} =V _{GS}	1.0	1.5	2.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =30V V _{GS} =0V		10	500	μA
				0.2	1.0	mA
Gate-source leakage current	I _{GSS}	V _{GS} =±16V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =25A V _{GS} =10V		12	17	mΩ
				7.5	10	mΩ
Forward transconductance	g _{fs}	I _D =25A V _{DS} =25V	22	45		S
Input capacitance	C _{iss}	V _{DS} =25V		2750	4130	pF
Output capacitance	C _{oss}	V _{GS} =0V		1300	1950	
Reverse transfer capacitance	C _{rss}	f=1MHz		600	900	
Turn-on time	t _{d(on)}	V _{CC} =15V R _G =10 Ω		13	20	ns
	t _r			55	83	
Turn-off time	t _{d(off)}	I _D =50A V _{GS} =10V		180	270	
	t _f			150	230	
Avalanche capability	I _{AV}	L=100μH T _{ch} =25°C	50			A
Diode forward on-voltage	V _{SD}	I _F =2xI _{DR} V _{GS} =0V T _{ch} =25°C		1.14	1.71	V
Reverse recovery time	t _{rr}	I _F =2xI _{DR} V _{GS} =0V		85	130	ns
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		0.17		μC

● Thermal characteristics

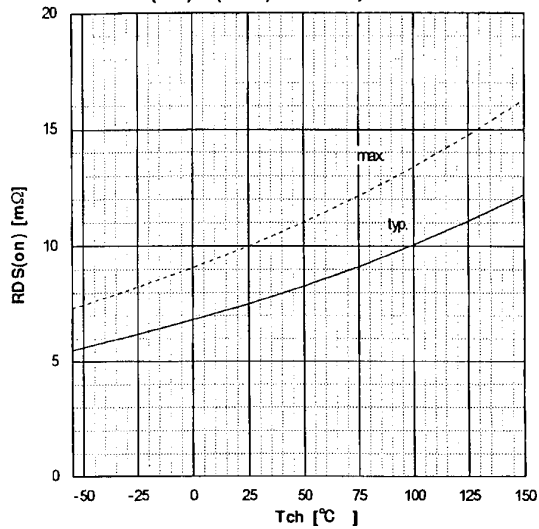
Item	Symbol	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}			2.08	°C/W
	R _{th(ch-a)}			75.0	°C/W

www.fujielectric.co.jp/fdt/scd

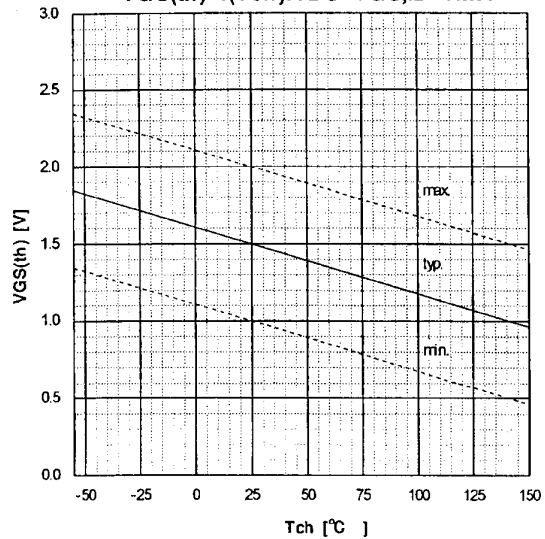
Characteristics



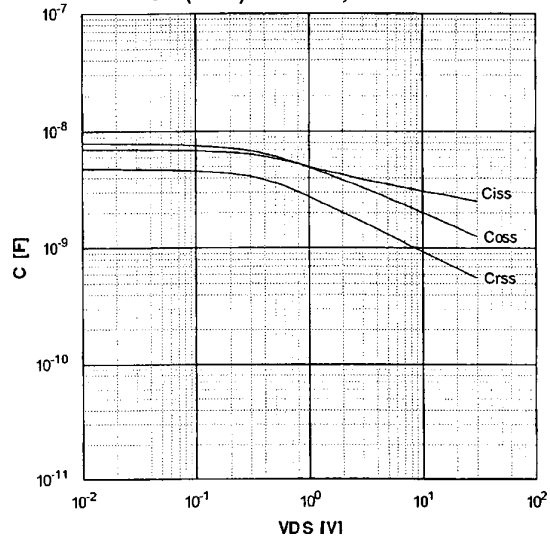
Drain-Source On-state Resistance
 $R_{DS(on)} = f(T_{ch}): I_D = 25A, V_{GS} = 10V$



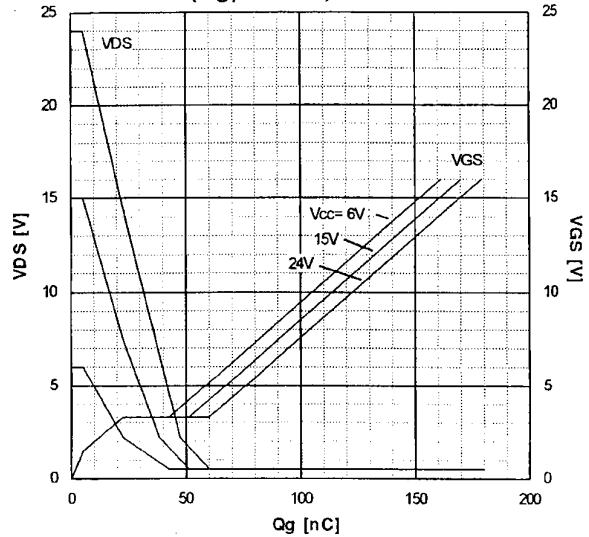
Gate Threshold Voltage
 $V_{GS(th)} = f(T_{ch}): V_{DS} = V_{GS}, I_D = 1mA$



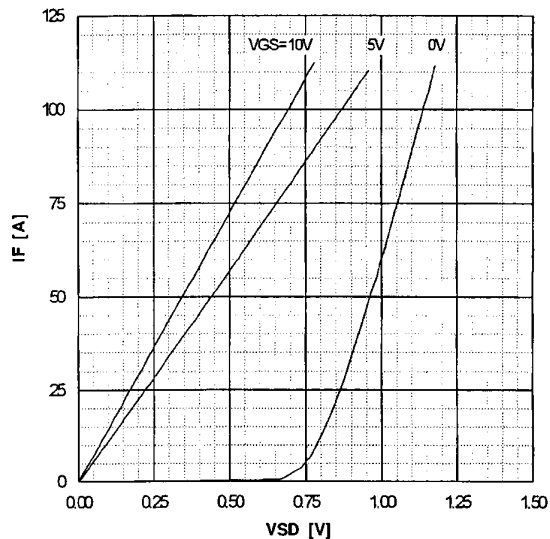
Typical Capacitance
 $C = f(V_{DS}): V_{GS} = 0V, f = 1MHz$



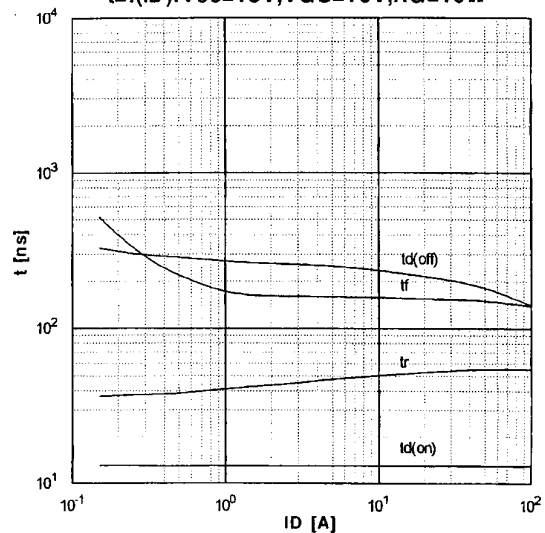
Typical Gate Charge Characteristics
 $V_{GS} = f(Q_g): I_D = 50A, T_{ch} = 25°C$



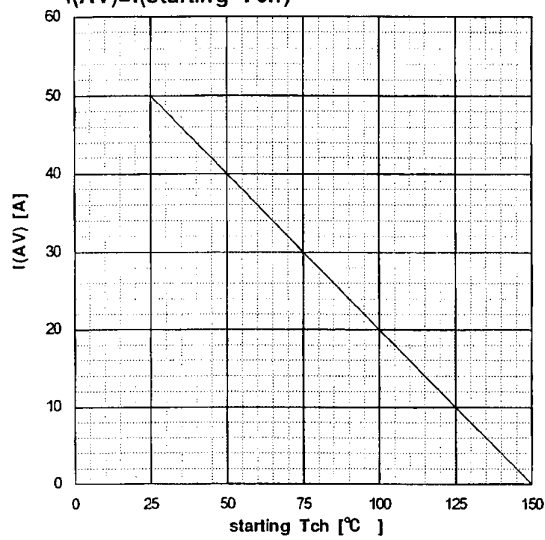
Typical Forward Characteristics of Reverse Diode
 $I_F = f(V_{SD}): 80\mu s \text{ pulse test}, T_{ch} = 25°C$



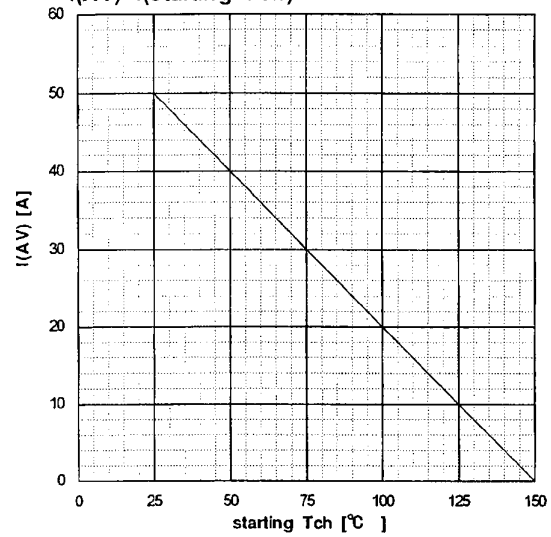
Typical Switching Characteristics vs. I_D
 $t = f(I_D): V_{CC} = 15V, V_{GS} = 10V, R_G = 10\Omega$



Maximum Avalanche Current vs. starting T_{ch}
 $I(AV)=f(\text{starting } T_{ch})$



Maximum Avalanche Current vs. starting T_{ch}
 $I(AV)=f(\text{starting } T_{ch})$



Transient Thermal impedance
 $Z_{th}(ch-c)=f(t)$ parameter: $D=t/T$

